

# NTZD3156C

## Small Signal MOSFET

20 V, 540 mA / -20 V, -430 mA

Complementary N- and P-Channel  
MOSFETs with Integrated Pull Up/Down  
Resistor and ESD Protection

### Features

- Leading Trench Technology for Low  $R_{DS(on)}$  Performance
- High Efficiency System Performance
- Low Threshold Voltage
- Integrated G-S Resistor on Both Devices
- ESD Protected Gate
- Small Footprint 1.6 x 1.6 mm
- These are Pb-Free Devices

### Applications

- Load/Power Switching with Level Shift
- Portable Electronic Products such as GPS, Cell Phones, DSC, PMP, Bluetooth Accessories

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			$V_{DSS}$	20	V
Gate-to-Source Voltage			$V_{GS}$	$\pm 6$	V
N-Channel Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	$I_D$	540	mA
		$T_A = 85^{\circ}\text{C}$		390	
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		570	
P-Channel Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$		-430	
		$T_A = 85^{\circ}\text{C}$		-310	
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		-455	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	$P_D$	250	mW
				$t \leq 5\text{ s}$	
Pulsed Drain Current	N-Channel	$t_p = 10\text{ }\mu\text{s}$	$I_{DM}$	1500	mA
	P-Channel			-750	
Operating Junction and Storage Temperature			$T_J, T_{STG}$	-55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode)			$I_S$	350	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			$T_L$	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq [1 oz] including traces).

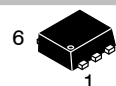
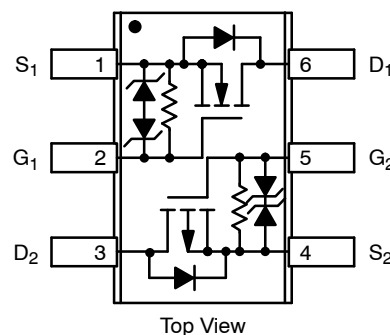


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<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Max	$I_D$ Max (Note 1)
N-Channel 20 V	0.55 $\Omega$ @ 4.5 V	540 mA
	0.7 $\Omega$ @ 2.5 V	
	0.9 $\Omega$ @ 1.8 V	
P-Channel -20 V	0.9 $\Omega$ @ -4.5 V	-430 mA
	1.2 $\Omega$ @ -2.5 V	
	2.0 $\Omega$ @ -1.8 V	

### PINOUT: SOT-563



SOT-563-6  
CASE 463A  
STYLE 9

ZC = Specific Device Code  
M = Date Code  
■ = Pb-Free Package

(Note: Microdot may be in either location)

### MARKING DIAGRAM



### ORDERING INFORMATION

Device	Package	Shipping†
NTZD3156CT1G	SOT-563	4000 / Tape & Reel
NTZD3156CT2G	SOT-563	4000 / Tape & Reel
NTZD3156CT5G	SOT-563	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NTZD3156C

## Thermal Resistance Ratings

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	116	$^{\circ}\text{C/W}$
Junction-to-Ambient – $t = 5$ s (Note 2)		304	

2. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	N	$V_{GS} = 0\text{ V}$	$I_D = 250\text{ }\mu\text{A}$	20		V
		P		$I_D = -250\text{ }\mu\text{A}$	-20		
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				20		mV/ $^{\circ}\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	N	$V_{GS} = 0\text{ V}, V_{DS} = 16\text{ V}$	$T_J = 25^{\circ}\text{C}$		1.0	$\mu\text{A}$
		P	$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$			-1.0	
		N	$V_{GS} = 0\text{ V}, V_{DS} = 16\text{ V}$	$T_J = 125^{\circ}\text{C}$		2.0	$\mu\text{A}$
		P	$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$			-5.0	
Gate-to-Source Leakage Current	$I_{GSS}$	N	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			$\pm 50$	$\mu\text{A}$
		P				$\pm 50$	

## ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	N	$V_{GS} = V_{DS}$	$I_D = 250\text{ }\mu\text{A}$	0.45	1.0	V
		P		$I_D = -250\text{ }\mu\text{A}$	-0.45	-1.0	
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				2.0		-mV/ $^{\circ}\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	N	$V_{GS} = 4.5\text{ V}, I_D = 540\text{ mA}$		0.19	0.55	$\Omega$
		P	$V_{GS} = -4.5\text{ V}, I_D = -430\text{ mA}$		0.39	0.9	
		N	$V_{GS} = 2.5\text{ V}, I_D = 500\text{ mA}$		0.26	0.7	
		P	$V_{GS} = -2.5\text{ V}, I_D = -300\text{ mA}$		0.53	1.2	
		N	$V_{GS} = 1.8\text{ V}, I_D = 350\text{ mA}$		0.36	0.9	
		P	$V_{GS} = -1.8\text{ V}, I_D = -150\text{ mA}$		0.72	2.0	
Forward Transconductance	$g_{FS}$	N	$V_{DS} = 10\text{ V}, I_D = 540\text{ mA}$		1.46		S
		P	$V_{DS} = -10\text{ V}, I_D = -430\text{ mA}$		1.18		

## CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	$C_{ISS}$	N	$f = 1\text{ MHz}, V_{GS} = 0\text{ V}$ $V_{DS} = 16\text{ V}$		72		pF
Output Capacitance	$C_{OSS}$				13		
Reverse Transfer Capacitance	$C_{RSS}$				10		
Input Capacitance	$C_{ISS}$	P	$f = 1\text{ MHz}, V_{GS} = 0\text{ V}$ $V_{DS} = -16\text{ V}$		93		
Output Capacitance	$C_{OSS}$				15		
Reverse Transfer Capacitance	$C_{RSS}$				11		

3. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$

# NTZD3156C

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
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### CHARGES, CAPACITANCES AND GATE RESISTANCE

Total Gate Charge	$Q_{G(TOT)}$	N	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}; I_D = 540\text{ mA}$		1.39	2.5	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate-to-Source Charge	$Q_{GS}$				0.26		
Gate-to-Drain Charge	$Q_{GD}$				0.39		
Total Gate Charge	$Q_{G(TOT)}$	P	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}; I_D = -430\text{ mA}$		1.49	2.5	
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate-to-Source Charge	$Q_{GS}$				0.3		
Gate-to-Drain Charge	$Q_{GD}$				0.37		

### SWITCHING CHARACTERISTICS ( $V_{GS} = V$ ) (Note 4)

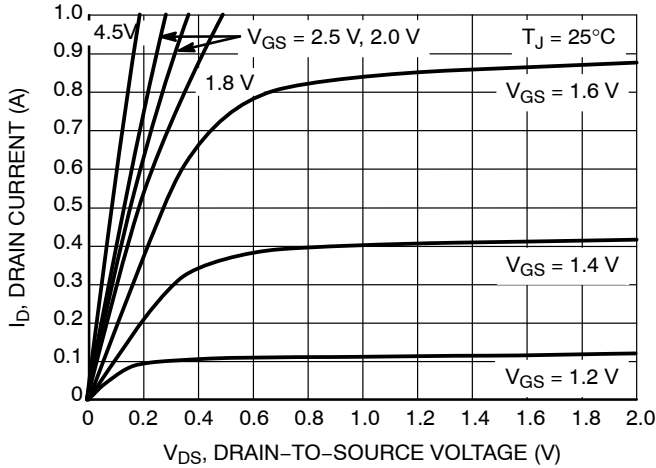
Turn-On Delay Time	$t_{d(ON)}$	N	$V_{GS} = 4.5\text{ V}, V_{DD} = 10\text{ V}, I_D = 540\text{ mA}, R_G = 10\ \Omega$		7.7		ns
Rise Time	$t_r$				5.3		
Turn-Off Delay Time	$t_{d(OFF)}$				21		
Fall Time	$t_f$				10		
Turn-On Delay Time	$t_{d(ON)}$	P	$V_{GS} = -4.5\text{ V}, V_{DD} = -10\text{ V}, I_D = -430\text{ mA}, R_G = 10\ \Omega$		9.2		
Rise Time	$t_r$				6.5		
Turn-Off Delay Time	$t_{d(OFF)}$				29		
Fall Time	$t_f$				19.5		

### Drain-Source Diode Characteristics

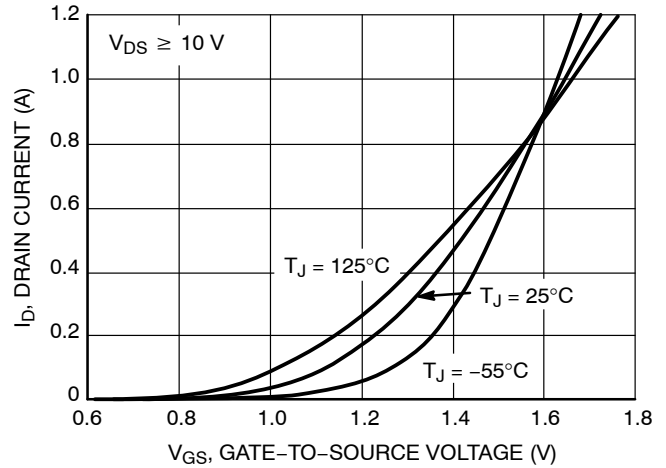
Forward Diode Voltage	$V_{SD}$	N	$V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	$I_S = 350\text{ mA}$		0.77	1.2	V
		P		$I_S = -350\text{ mA}$		-0.77	-1.2	
		N	$V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$	$I_S = 350\text{ mA}$		0.65		
		P		$I_S = -350\text{ mA}$		0.63		
Reverse Recovery Time	$t_{RR}$	N	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}$	$I_S = 350\text{ mA}$		9.4		ns
		P		$I_S = -350\text{ mA}$		14.6		

4. Switching characteristics are independent of operating junction temperatures

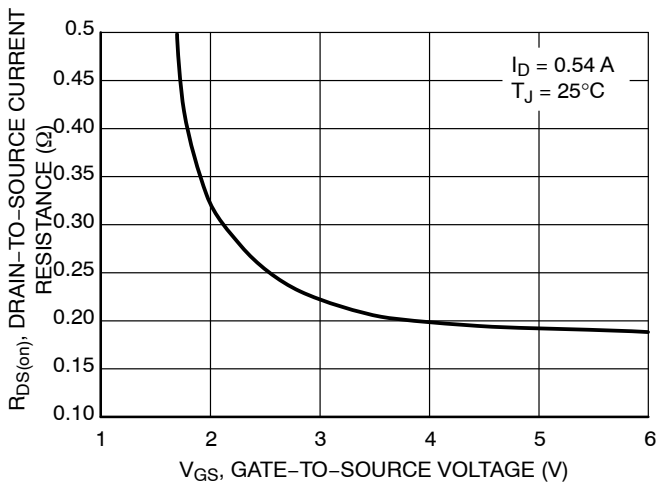
**N-CHANNEL TYPICAL PERFORMANCE CURVES** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)



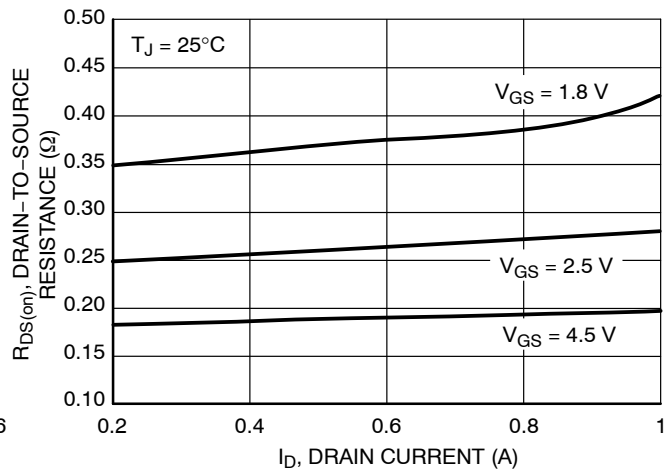
**Figure 1. On-Region Characteristics**



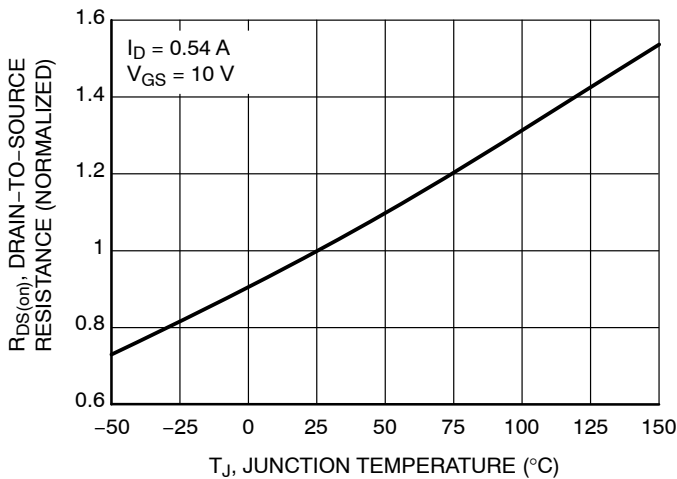
**Figure 2. Transfer Characteristics**



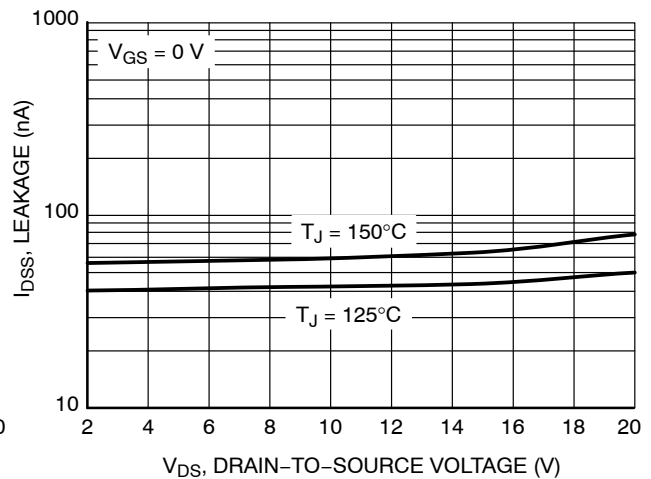
**Figure 3. On-Resistance versus Gate-to-Source Voltage**



**Figure 4. On-Resistance versus Drain Current and Gate Voltage**

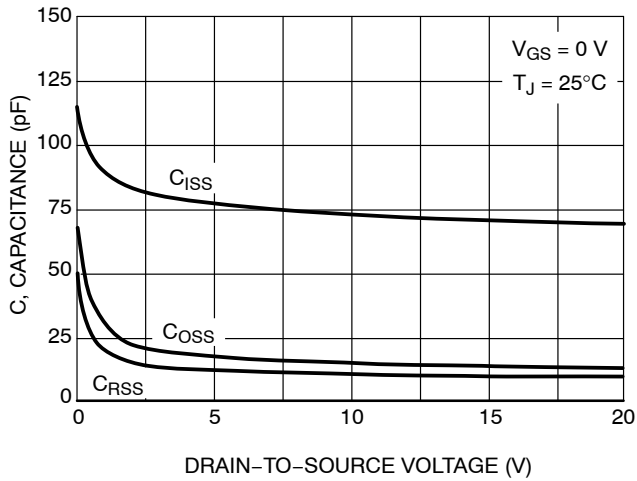


**Figure 5. On-Resistance Variation with Temperature**

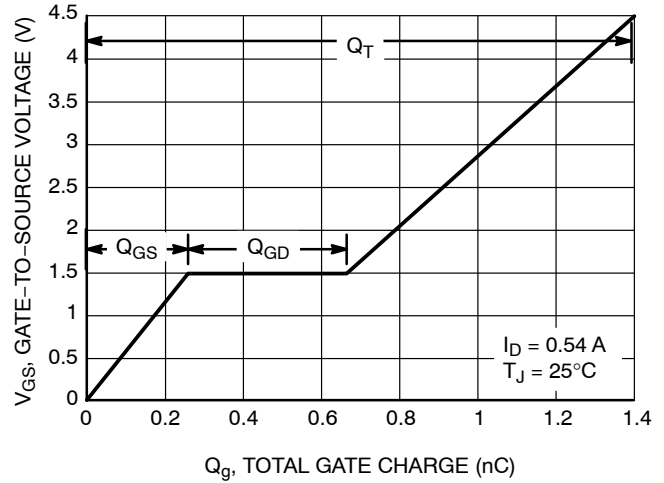


**Figure 6. Drain-to-Source Leakage Current versus Voltage**

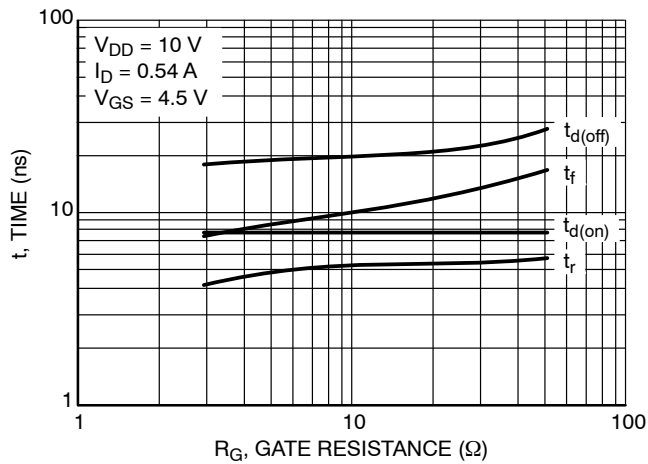
**N-CHANNEL TYPICAL PERFORMANCE CURVES** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)



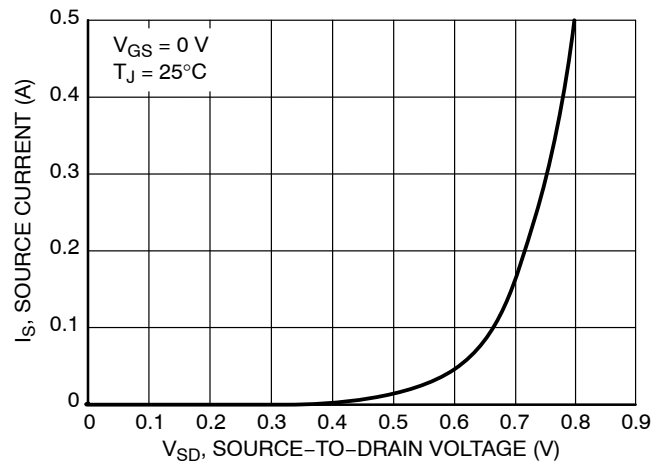
**Figure 7. Capacitance Variation**



**Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge**

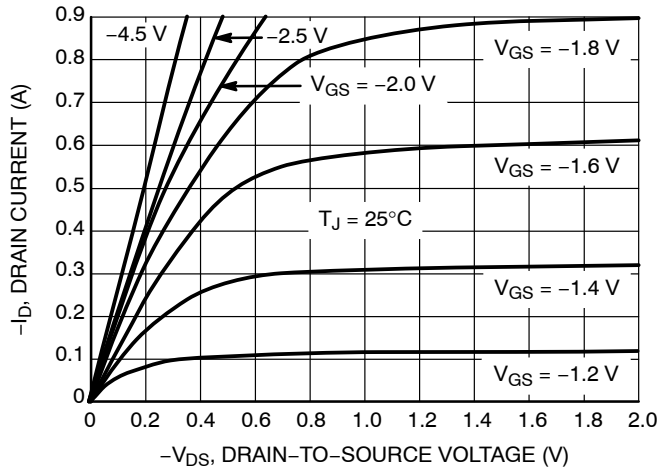


**Figure 9. Resistive Switching Time Variation versus Gate Resistance**

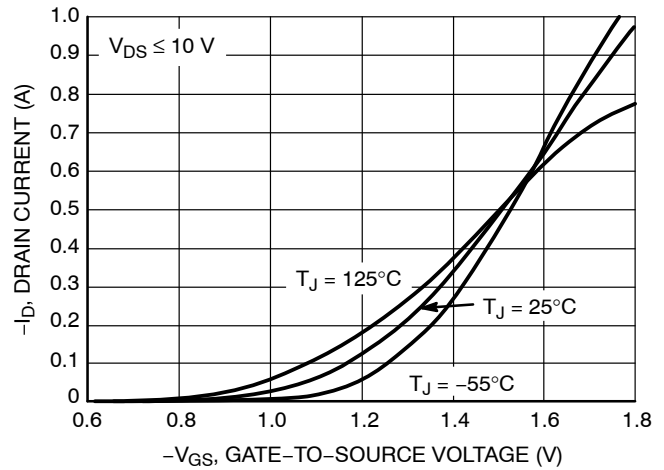


**Figure 10. Diode Forward Voltage versus Current**

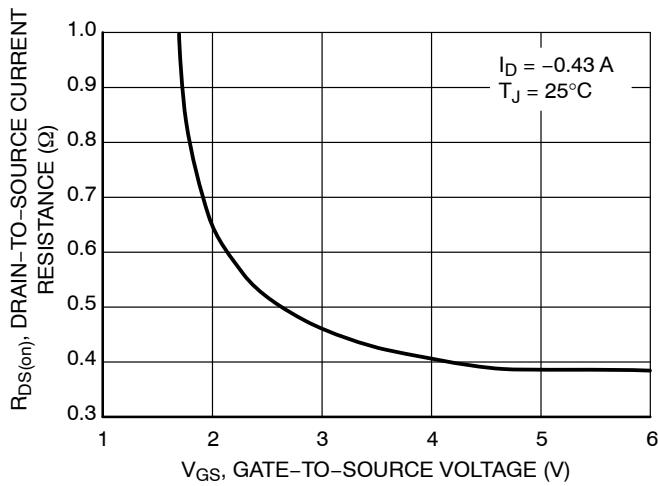
**P-CHANNEL TYPICAL PERFORMANCE CURVES** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)



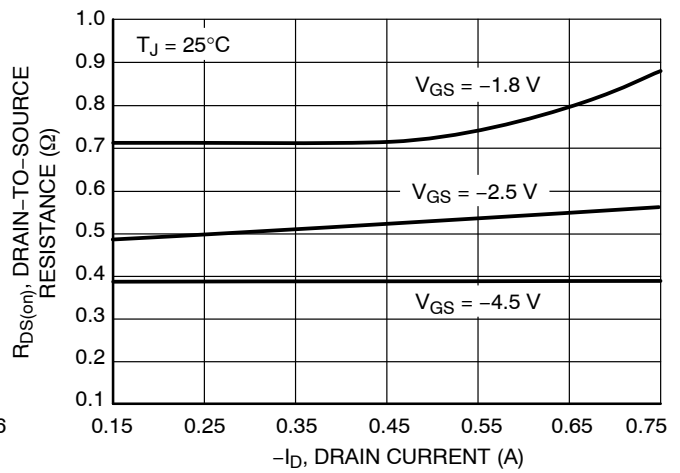
**Figure 11. On-Region Characteristics**



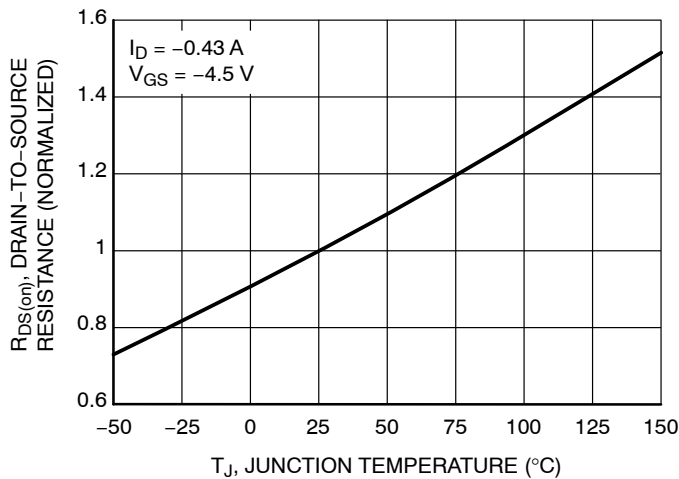
**Figure 12. Transfer Characteristics**



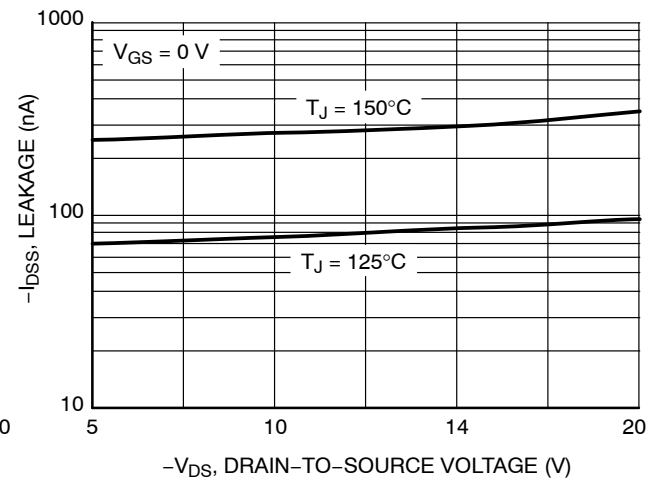
**Figure 13. On-Resistance versus Gate-to-Source Voltage**



**Figure 14. On-Resistance versus Drain Current and Gate Voltage**

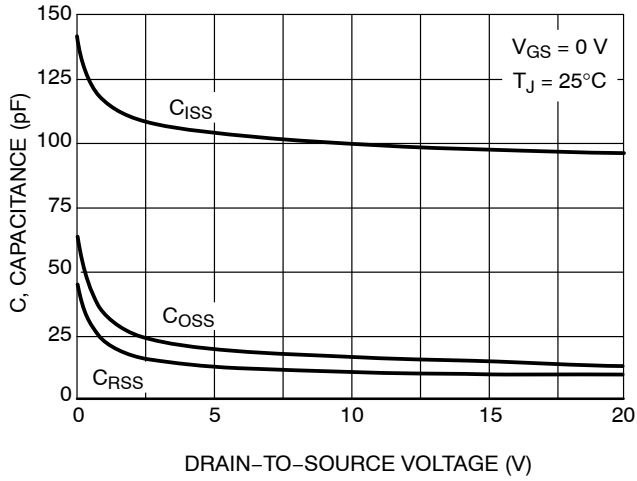


**Figure 15. On-Resistance Variation with Temperature**

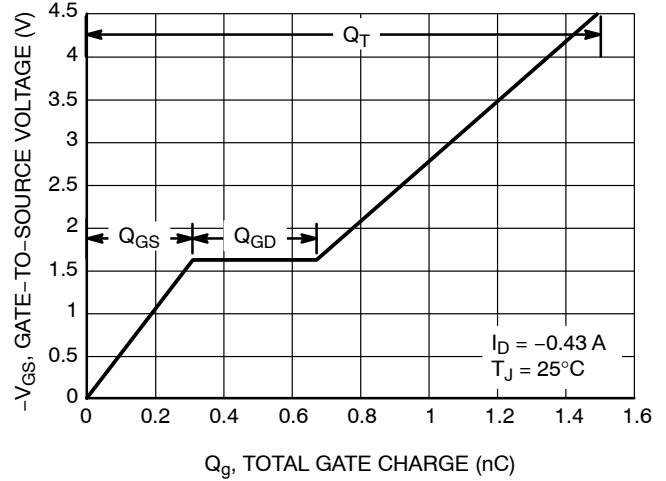


**Figure 16. Drain-to-Source Leakage Current versus Voltage**

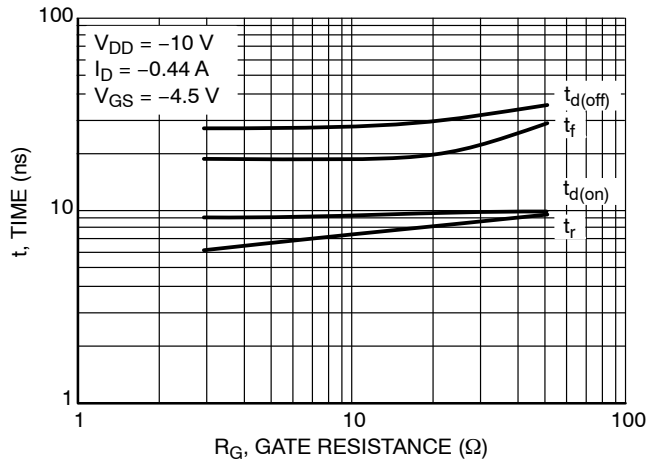
**P-CHANNEL TYPICAL PERFORMANCE CURVES** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)



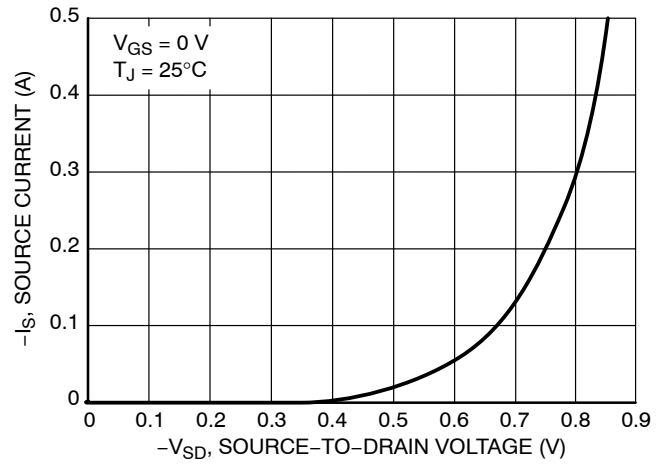
**Figure 17. Capacitance Variation**



**Figure 18. Gate-to-Source and Drain-to-Source Voltage versus Total Charge**



**Figure 19. Resistive Switching Time Variation versus Gate Resistance**



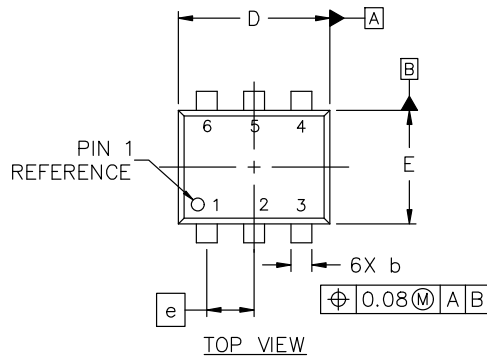
**Figure 20. Diode Forward Voltage versus Current**


**SOT-563-6 1.60x1.20x0.55, 0.50P**  
**CASE 463A**  
**ISSUE J**

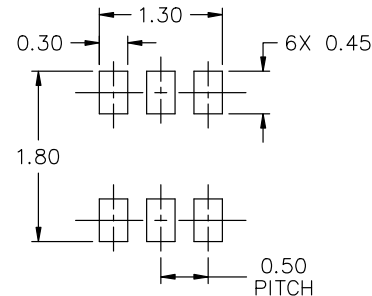
15 FEB 2024

## NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

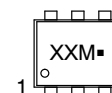


DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30



## RECOMMENDED MOUNTING FOOTPRINT\*

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

**GENERIC MARKING DIAGRAM\***


XX = Specific Device Code

M = Month Code

▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:  
PIN 1. EMITTER 1  
2. BASE 1  
3. COLLECTOR 2  
4. EMITTER 2  
5. BASE 2  
6. COLLECTOR 1

STYLE 2:  
PIN 1. EMITTER 1  
2. EMITTER 2  
3. BASE 2  
4. COLLECTOR 2  
5. BASE 1  
6. COLLECTOR 1

STYLE 3:  
PIN 1. CATHODE 1  
2. CATHODE 1  
3. ANODE/ANODE 2  
4. CATHODE 2  
5. CATHODE 2  
6. ANODE/ANODE 1

STYLE 4:  
PIN 1. COLLECTOR  
2. COLLECTOR  
3. BASE  
4. EMITTER  
5. COLLECTOR  
6. COLLECTOR

STYLE 5:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE  
4. ANODE  
5. CATHODE  
6. CATHODE

STYLE 6:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. CATHODE  
5. CATHODE  
6. CATHODE

STYLE 7:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. CATHODE  
5. ANODE  
6. CATHODE

STYLE 8:  
PIN 1. DRAIN  
2. DRAIN  
3. GATE  
4. SOURCE  
5. DRAIN  
6. DRAIN

STYLE 9:  
PIN 1. SOURCE 1  
2. GATE 1  
3. DRAIN 2  
4. SOURCE 2  
5. GATE 2  
6. DRAIN 1

STYLE 10:  
PIN 1. CATHODE 1  
2. N/C  
3. CATHODE 2  
4. ANODE 2  
5. N/C  
6. ANODE 1

STYLE 11:  
PIN 1. EMITTER 2  
2. BASE 2  
3. COLLECTOR 1  
4. EMITTER 1  
5. BASE 1  
6. COLLECTOR 2

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<b>DESCRIPTION:</b>	<b>SOT-563-6 1.60x1.20x0.55, 0.50P</b>	<b>PAGE 1 OF 1</b>

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